

1 13. (New) A method for etching as set forth in claim 12 including injecting said XeF₂ gas on a
2 surface of said silicon wafer with a viscous laminar downflow.

1 14. (New) A method for etching as set forth in claim 12 including the additional step of
2 controlling internal pressure of the loading chamber at a level between sublimation pressure
3 of XeF₂ and atmospheric pressure to prevent sublimation of residual XeF₂ in the loading
4 chamber.

REMARKS

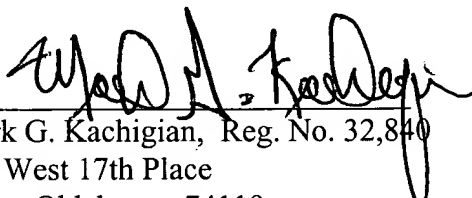
Claims 1-7 have been canceled and new claims 8 through 14 have been added. Applicant herein respectfully requests the Examiner to review and allow the enclosed new set of claims.

If any further issues remain, a telephone conference interview with the Examiner is requested.

Respectfully Submitted

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